

Docket No.: 052725-0025



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
Masahiro NAKAYAMA, et al.	:	Confirmation Number: 6895
Application No.: 10/665,483	:	Group Art Unit: 3723
Filed: September 22, 2003	:	Examiner: ACKUN, Jacob K.

For: NITRIDE SEMICONDUCTOR WAFER AND METHOD OF PROCESSING NITRIDE SEMICONDUCTOR WAFER

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

This Information Disclosure Statement is being filed under Rule 37 CFR 1.97(i), wherein applicants are submitting references before the grant of a patent to be placed in the file.

Accordingly, copies of the references as listed on the attached Form PTO-1449 are submitted herewith for placement in the file. No certification or fees are deemed necessary.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Please recognize our Customer No. 20277 as our correspondence address.

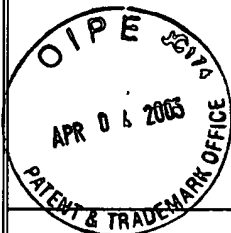
INFORMATION DISCLOSURE CITATION IN AN APPLICATION

 ATTY. DOCKET NO.
052775-0025

 SERIAL NO.
10/665,483

 APPLICANT
Masahiro NAKAYAMA, et al.

 FILING DATE
**September 22,
2003**

 GROUP
3723


(PTO-1449)

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US 2002/0185054 A1	12/12/2002	Xu et al.	
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		EP 0 966 047 A2	12/22/1999	SUMITOMO ELECTRIC INDUSTRIES, LTD.		X	
		WO 01/68955 A1	09/20/2001	ADVANCED TECHNOLOGY MATERIALS, INC.		X	
		EP 0 782 179 A2	07/02/1997	SHIN-ETSU HANDOTAI CO., LTD.		X	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		BARDWELL, J.A. et al. "Ultraviolet photoenhanced wet etching of GaN in K ₂ S ₂ O ₈ solution." Journal of Applied Physics, American Institute of Physics, Volume 89, Number 7, April 1, 2001, XP012053261, pp. 4142-4149
		WEYHER, J.L., et al. "Chemical polishing of bulk and epitaxial GaN." Journal of Crystal growth, 182, 1997, XP004100368 pp. 17-22

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.